

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 8 A, 650 V, D2, D2PAK-2L

## FFSB0865B-F085

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 33 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

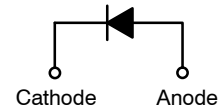
- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

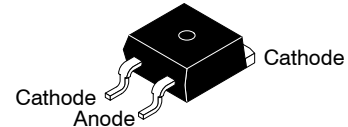
Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	650	V
Single Pulse Avalanche Energy (T <sub>J</sub> = 25°C, I <sub>L(pk)</sub> = 11.5 A, L = 0.5 mH, V = 50 V)	E <sub>AS</sub>	33	mJ
Continuous Rectified Forward Current	@ T <sub>C</sub> < 147	I <sub>F</sub>	8.0 A
	@ T <sub>C</sub> < 135		10.1
Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C t <sub>p</sub> = 10 μs	I <sub>FM</sub>	577 A
	T <sub>C</sub> = 150°C t <sub>p</sub> = 10 μs		533
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	T <sub>C</sub> = 25°C t <sub>p</sub> = 8.3 ms	I <sub>FSM</sub>	56 A
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>tot</sub>	73 W
	T <sub>C</sub> = 150°C		12
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

V <sub>RRM</sub>	I <sub>F</sub>
650 V	8.0 A

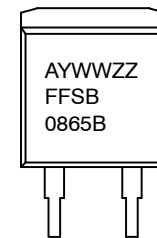


Schottky Diode



D<sup>2</sup>PAK2 (TO-263-2L)  
CASE 418BK

### MARKING DIAGRAM



- A = Assembly Plant Code
- YWW = Date Code (Year & Week)
- ZZ = Lot Code
- FFSB0865B = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSB0865B–F085

## THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max.	$R_{\theta JC}$	2.05	°C/W

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### ON CHARACTERISTICS

Forward Voltage	$V_F$	$I_F = 8.0\text{ A}, T_J = 25^\circ\text{C}$		1.39	1.7	V
		$I_F = 8.0\text{ A}, T_J = 125^\circ\text{C}$		1.55	2.0	
		$I_F = 8.0\text{ A}, T_J = 175^\circ\text{C}$		1.71	2.4	
Reverse Current	$I_R$	$V_R = 650\text{ V}, T_J = 25^\circ\text{C}$		0.5	40	$\mu\text{A}$
		$V_R = 650\text{ V}, T_J = 125^\circ\text{C}$		1.0	80	
		$V_R = 650\text{ V}, T_J = 175^\circ\text{C}$		2.0	160	

### CHARGES, CAPACITANCES & GATE RESISTANCE

Total Capacitive Charge	$Q_C$	$V_C = 400\text{ V}$		22		nC
	$C_{tot}$	$V_R = 1\text{ V}, f = 100\text{ kHz}$		336		pF
		$V_R = 200\text{ V}, f = 100\text{ kHz}$		39		
		$V_R = 400\text{ V}, f = 100\text{ kHz}$		30		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSB0865B–F085	FFSB0865B	D <sup>2</sup> PAK2 (TO–263–2L)	Tape & Reel†	330 mm	24 mm	800 Units

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

TYPICAL CHARACTERISTICS



Figure 1. Forward Characteristics

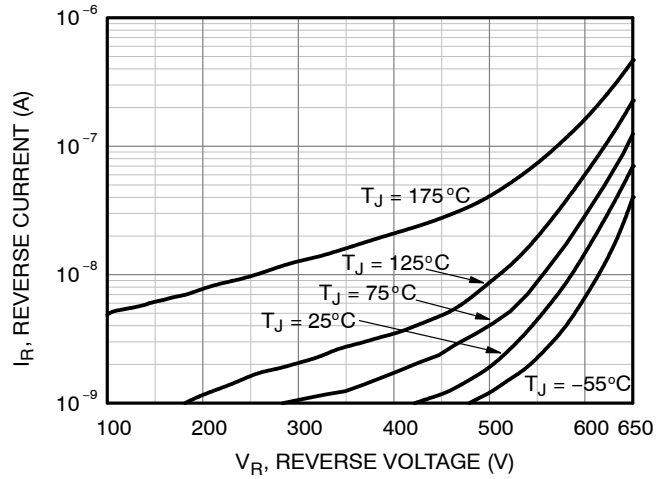


Figure 2. Reverse Characteristics

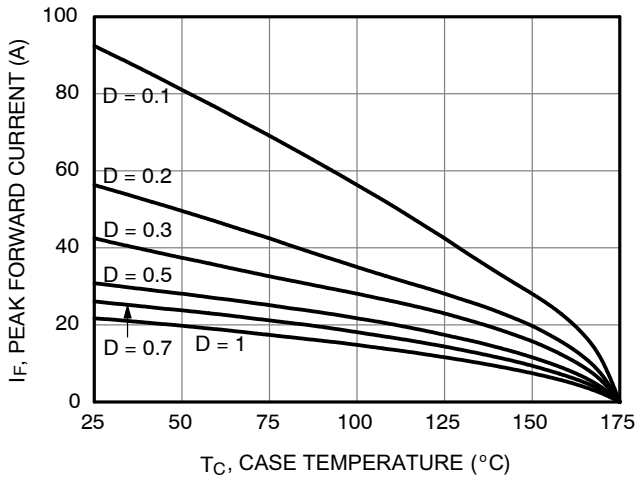


Figure 3. Current Derating

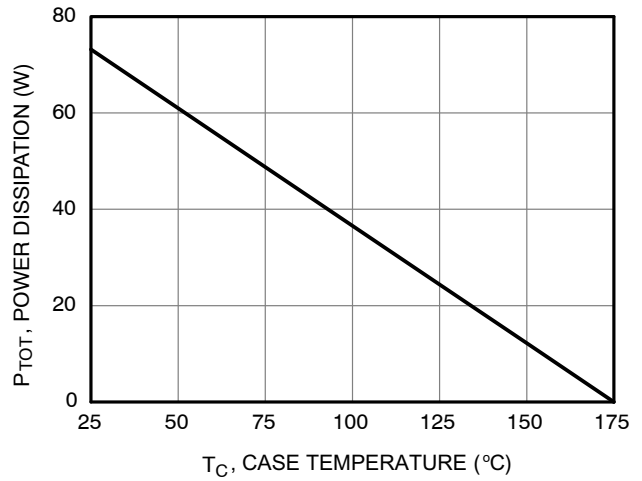


Figure 4. Power Derating

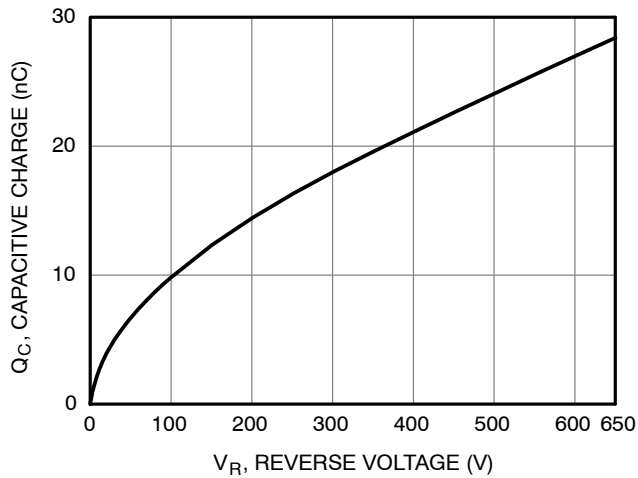


Figure 5. Capacitive Charge vs. Reverse Voltage

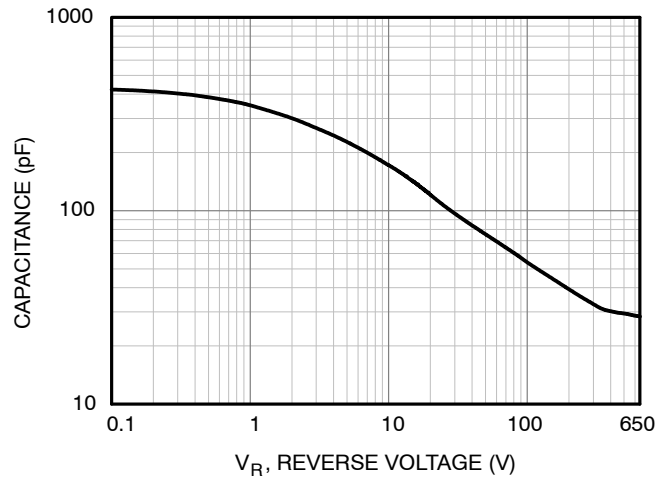


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

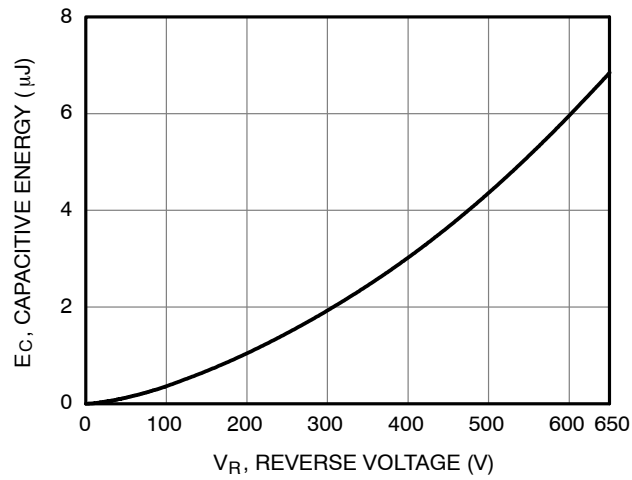


Figure 7. Capacitance Stored Energy

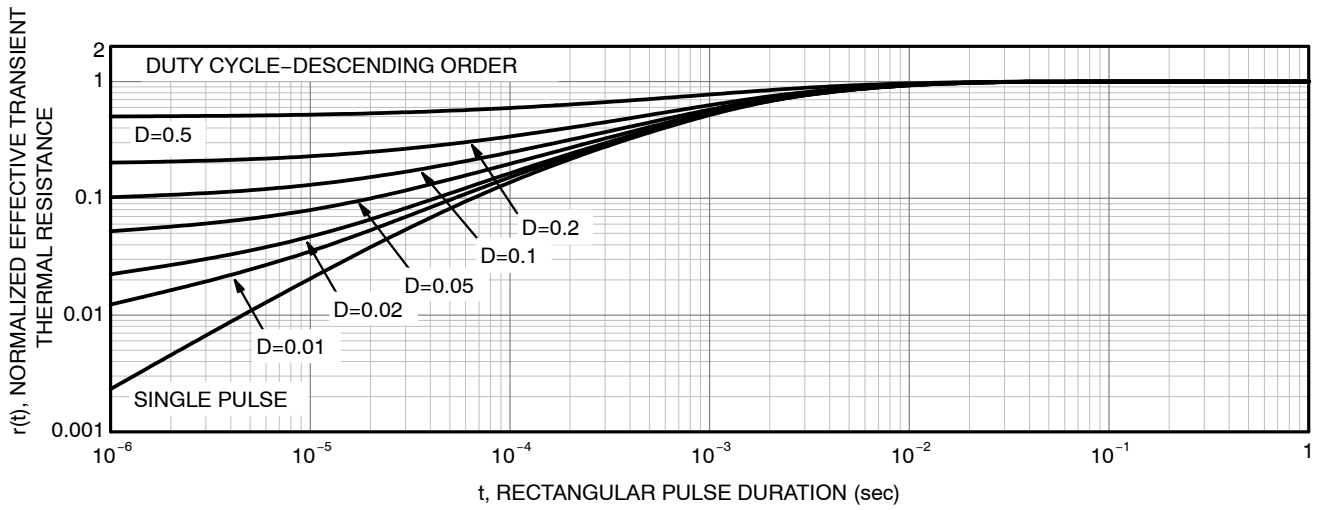
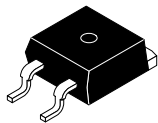


Figure 8. Junction-to-Case Transient Thermal Response

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS



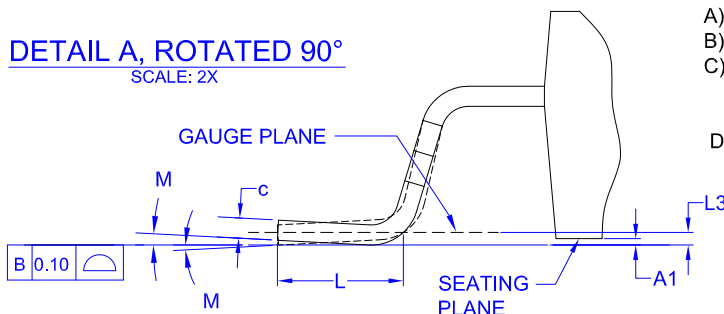
**D<sup>2</sup>PAK2 (TO-263-2L)**  
**CASE 418BK**  
**ISSUE O**

DATE 02 AUG 2018

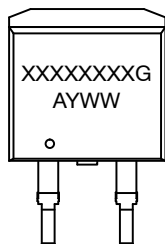


NOTES: UNLESS OTHERWISE SPECIFIED  
 A) ALL DIMENSIONS ARE IN MILLIMETERS.  
 B) REFERENCE JEDEC, TO-263, VARIATION AB.  
 C) DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.  
 D) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N

**DETAIL A, ROTATED 90°**  
 SCALE: 2X



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**LAND PATTERN RECOMMENDATION**  
 UNLESS NOTED, ALL DIMS TYPICAL

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.06	4.57	4.83
A1	0.00	0.10	0.25
b	0.51	0.81	0.99
c	0.30	0.407	0.74
c2	1.14	1.30	1.65
D	8.38	8.69	9.65
D1	7.30	7.80	8.30
E	9.65	10.16	10.67
E1	8.00	8.62	9.00
e	5.08 BSC		
H	14.60	15.35	15.88
L	1.78	2.54	2.79
L1	0.90	1.29	1.68
L2	0.00	0.15	0.25
L3	0.25 BSC		
M	0°	4°	8°

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<b>DESCRIPTION:</b>	<b>D<sup>2</sup>PAK2 (TO-263-2L)</b>	<b>PAGE 1 OF 1</b>

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